

# BRCS016N03DP

Rev.A Jan.-2022

## 描述 / Descriptions

TO-252 塑封封装 N 沟道场效应管。

N-CHANNEL MOSFET in a TO-252 Plastic Package.

## 特征 / Features

$R_{DS(on)}$ 小, 门电荷低,  $C_{rss}$ 小, 开关速度快, 无卤产品。

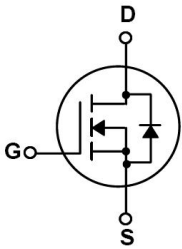
Low  $R_{DS(on)}$ , low gate charge, low  $C_{rss}$ , fast switching, Halogen-free Product.

## 用途 / Applications

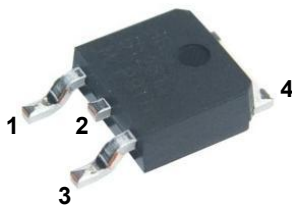
用于低压电路如: 汽车电路、DC/DC 转换、便携式产品的电源高效转换。

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1 : G

PIN 2 : D

PIN 3 : S

PIN 4 : D

## 放大及印章代码 / $h_{FE}$ Classifications & Marking

见印章说明。

See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	$V_{DSS}$	30	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	125	A
Drain Current - Pulsed	$I_{DM}$	213	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Avalanche Current	$I_{AS}$	24	A
Single Pulsed Avalanche Energy(L=0.5mH)	$E_{AS}$	302.4	mJ
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	156	W
Storage Temperature Range	$T_{stg}$	-55 to 150	$^\circ\text{C}$
Thermal Resistance-Junction to Ambient	$t \leq 10s$	$R_{\theta JA}$	20
	Steady-State		50
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	0.8

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$ $I_D=250\mu A$	30	35		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V$ $V_{GS}=0V$			1.0	$\mu A$
		$V_{DS}=24V$ $T_C=150^\circ\text{C}$			10	
Gate-Body Leakage Current Forward	$I_{GSS}$	$V_{GS}=\pm 20V$ $V_{DS}=0V$			$\pm 0.1$	$\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.6	2.8	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		1.6	2.0	m $\Omega$
		$V_{GS}=4.5V$ $I_D=10A$		2.3	3.0	
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V$ $I_S=1A$			1.2	V
Gate resistance	$R_g$	$V_{GS}=0V$ $V_{DS}=0V,$ $f=1MHz$		1.8		$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		8500		pF
Output Capacitance	$C_{oss}$			890		
Reverse Transfer Capacitance	$C_{rss}$			670		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V,$ $V_{DS}=15V,$ $I_D=20A$		60		nC
Total Gate Charge	$Q_{g(4.5V)}$			28		
Gate Source Charge	$Q_{gs}$			12		
Gate Drain Charge	$Q_{gd}$			9.5		

## 电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75\ \Omega$ $R_{GEN}=3\ \Omega$		12.5		ns
Turn-On Rise Time	$t_r$			6.0		
Turn-Off Delay Time	$t_{d(off)}$			47		
Turn-Off Fall Time	$t_f$			10.5		

**电参数曲线图 / Electrical Characteristic Curve**

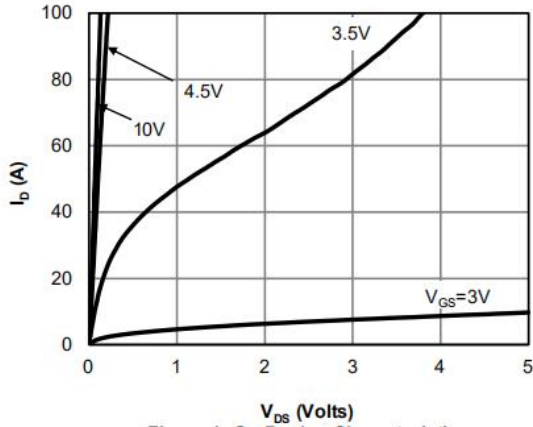


Figure 1: On-Region Characteristics

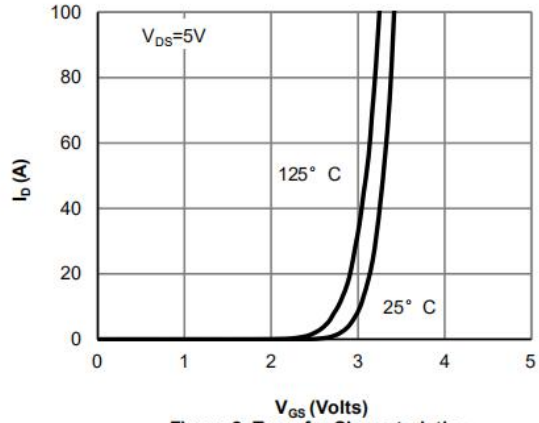


Figure 2: Transfer Characteristics

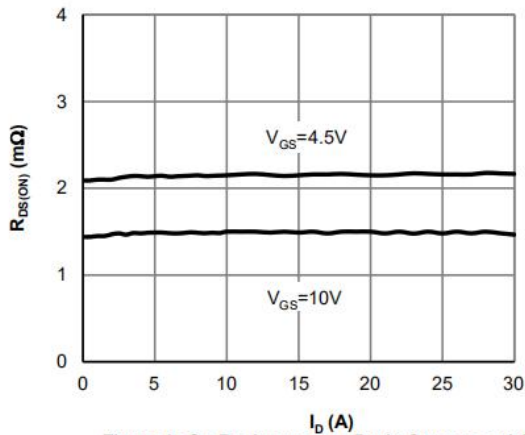


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

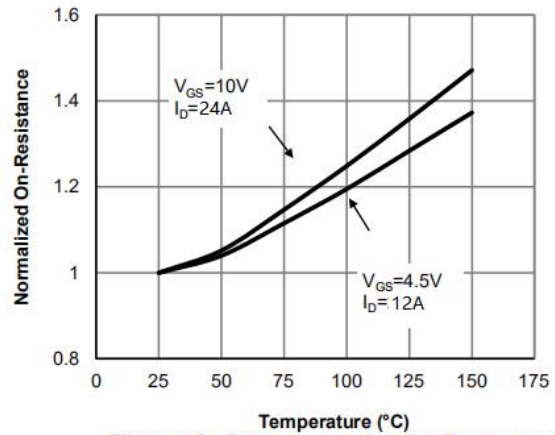


Figure 4: On-Resistance vs. Junction Temperature

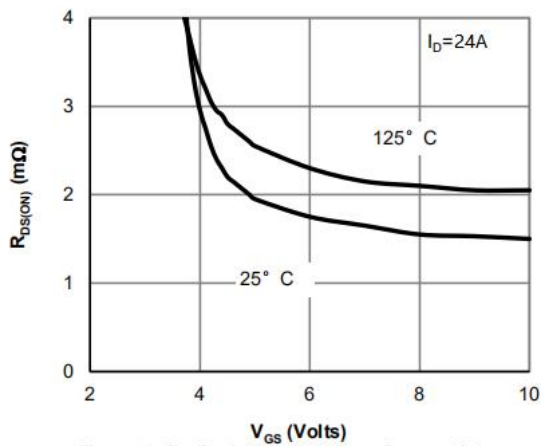


Figure 5: On-Resistance vs. Gate-Source Voltage

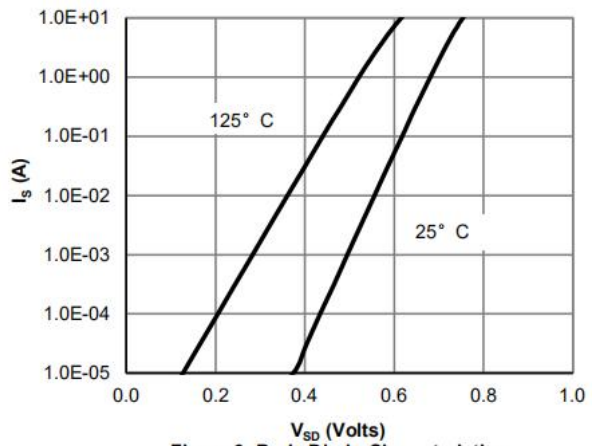
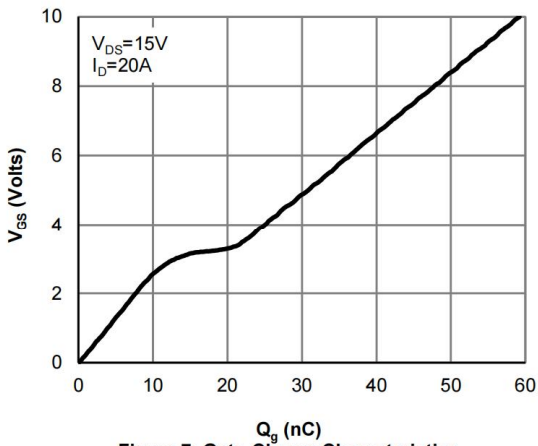
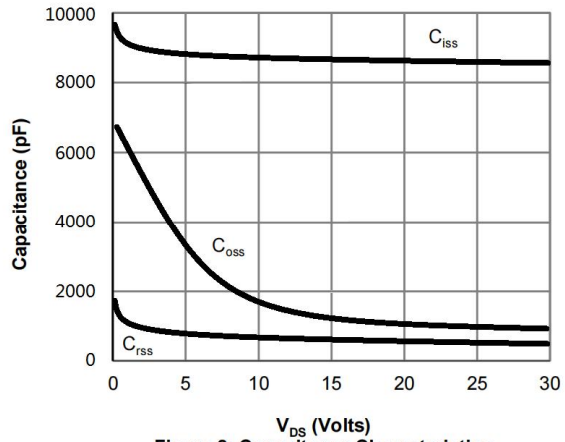


Figure 6: Body-Diode Characteristics

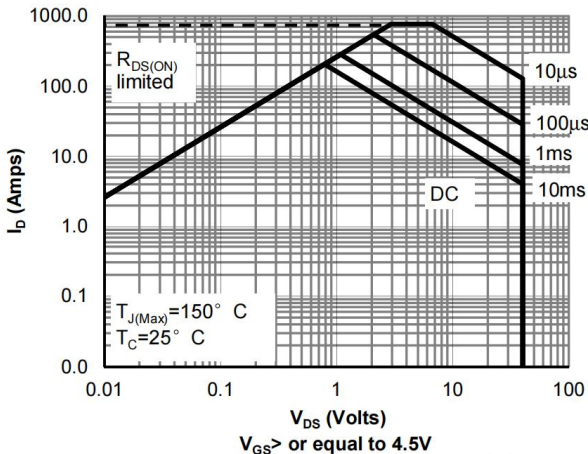
**电参数曲线图 / Electrical Characteristic Curve**



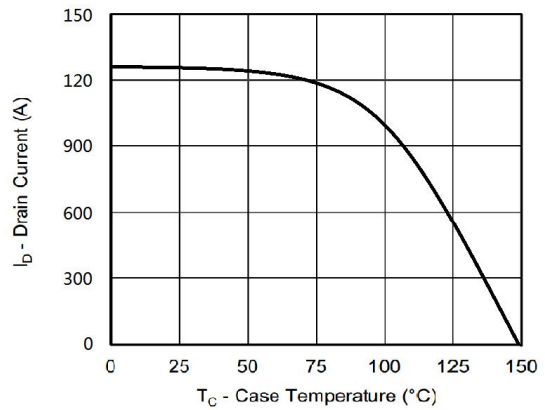
**Figure 7: Gate-Charge Characteristics**



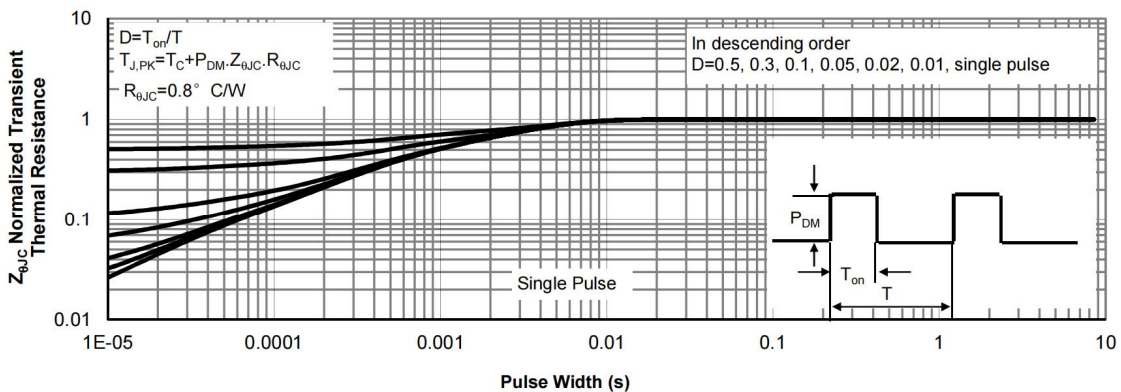
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area**

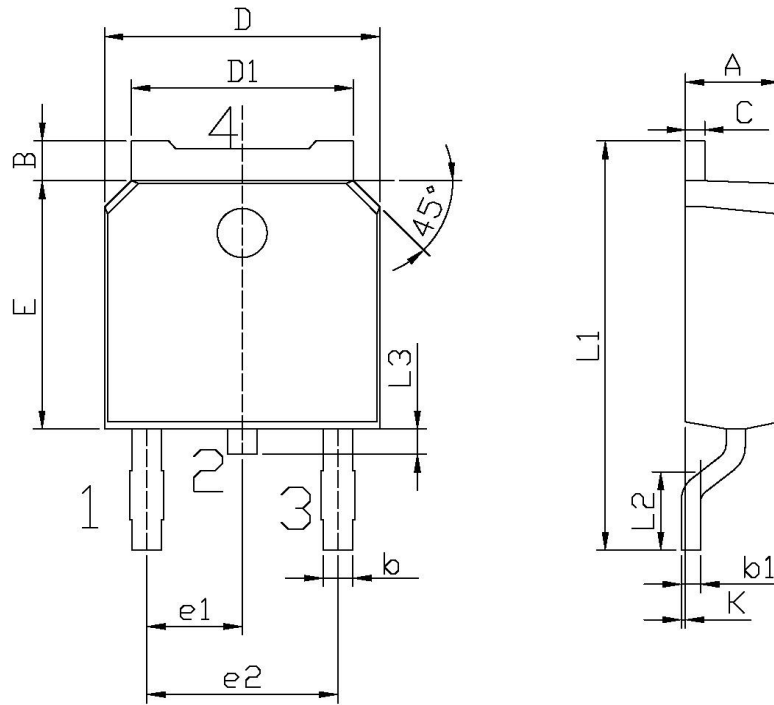


**Figure 10: Maximum Continuous Drain Current vs Case Temperature**



**Figure 11: Normalized Maximum Transient Thermal Impedance**

外形尺寸图 / Package Dimensions



单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.70	2.00
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252

## 印章说明 / Marking Instructions



说明：

BR： 为公司代码

016N03： 为型号代码

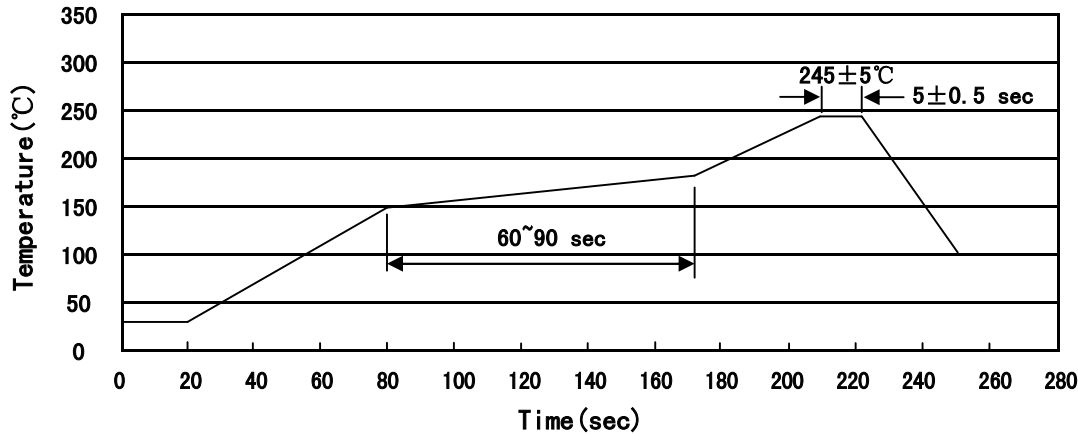
\*\*\*\*： 为生产批号代码，随生产批号变化。

Note:

BR: Company Code

016N03: Product Type Code.

\*\*\*\*: Lot No. Code, code change with Lot No.

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**


说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-252	2,500	2	5,000	6	30,000	13" ×16	360×360×50	380×335×366

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

**使用说明 / Notices**